

In the Specification

Delete the paragraph beginning on page 3, line 21, and replace it with the following paragraph:

The above and other objects, which will be apparent to those skilled in the art, are achieved in the present invention, which, is directed to in a first aspect a method of improving adhesion between an insulating layer and a capping layer in a process for making electronic components.

Delete the paragraph beginning on page 5, line 5, and replace it with the following paragraph:

In so doing, this treatment gas contacts the heated surface for adsorption of the gas onto the surface of the insulating layer to form a treated surface area thereof while maintaining an original thickness of the insulating layer. A capping layer is then deposited directly over the insulating layer wherein the treated surface area of the insulating layer improves adhesion between the insulating and the capping layers to prevent delamination therebetween during subsequent processing steps.

Delete the paragraph beginning on page 11, line 3, and replace it with the following paragraph:

Once the treated surface area 35 of insulating layer 30 is formed, and optionally oxidized and/or carbonized, a capping layer 40 is provided directly and entirely over this treated surface area 35, whereby the treated surface area 35 of the invention significantly improves adhesion between it and the capping layer 40. The capping layer 40 may be comprise a material including, but not limited to, silicon oxide, silicon

carbide, silicon nitride, and the like, deposited by known techniques to a thickness ranging from about 2 nm to about 100 nm.